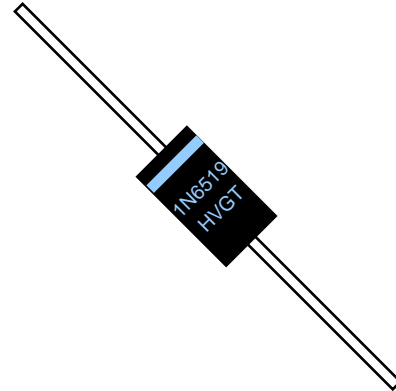




High reliability resin molded type high voltage diode in small size package which is sealed a multilayered mesa type silicon chip by epoxy resin.

Outline Drawings :



Features

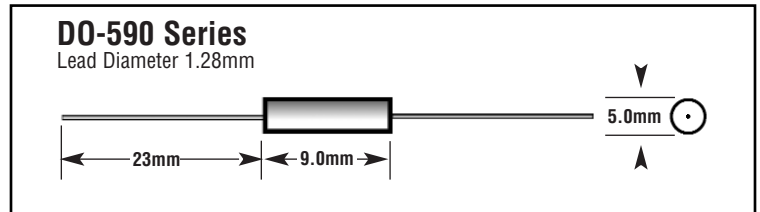
- High speed switching
- Epoxy resin molded in vacuum, Have anticorrosion in the surface
- High surge resistivity for CRT discharge
- High reliability design
- Avalanche characteristic

Applications

- X light Power supply
- Laser
- Voltage doubler circuit
- Microwave emission power
- General purpose high voltage rectifier, Voltage multiplier assembly.

Maximum Ratings and Characteristics

- Absolute Maximum Ratings



Items	Symbols	Condition	1N6519	Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_a=25^{\circ}C,$	10	kV
Average Output Current	I_o	$T_a=25^{\circ}C,$ Resistive Load	500	mA
Surge Current	I_{FSM}	$T_a=25^{\circ}C,$ 8.3 ms	25	A _{peak}
Junction Temperature	T_j		125	$^{\circ}C$
Allowable Operation Case Temperature	T_c		125	$^{\circ}C$
Storage Temperature	T_{stg}		-55 to +165	$^{\circ}C$

- Electrical Characteristics ($T_a=25^{\circ}C$ Unless otherwise specified)

Items	Symbols	Conditions	1N6519	Units
Maximum Forward Voltage Drop	V_F	at $25^{\circ}C,$ $I_F = I_{F(AV)}$	13	V
Maximum Reverse Current	IR1	at $25^{\circ}C,$ $V_R = V_{RRM}$	1.0	μA
	IR2	at $100^{\circ}C,$ $V_R = V_{RRM}$	25	μA
Maximum Reverse Recovery Time	T_{rr}	at $25^{\circ}C;$ $I_F = 0.5A;$ $I_R = 1.0A;$ $I_{rr} = 0.25A;$	70	nS
Junction Capacitance	C_j	at $25^{\circ}C;$ $V_R = 0V,$ $f = 1kHz$	8.0	pF

